

**AMENDMENTS TO THE CLAIMS**

**This listing of claims will replace all prior versions and listings of claims in the application:**

**LISTING OF CLAIMS:**

Claim 1 (currently amended): An electrode for a light-emitting semiconductor device, formed on a surface of a p-type GaN-base compound semiconductor, comprising:

a light-permeable electrode comprised of a first layer containing Au contacting formed to come into contact with the surface of the p-type GaN-base compound semiconductor, and a second layer, having a thickness in a range of 1 nm to 60 nm, formed on the first layer and comprising a light-permeable metal oxide containing an oxide of Ni; and

a wire-bonding electrode that is ~~in electrical contact~~ electrically contacting with the light-permeable electrode ~~that is in electrical contact with the light-permeable electrode and is formed to come into partial contact with~~ partially contacting the surface of the p-type GaN-base compound semiconductor with at least a region in contact with the semiconductor having a higher contact resistance per unit area with respect to the semiconductor than a region of the light-permeable electrode in contact with the semiconductor.

Claim 2 (currently amended): The electrode according to claim 1, wherein ~~the region of the wire-bonding electrode in contact with~~ this contacting the p-type GaN-base compound semiconductor having a higher contact resistance per unit area with respect to the p-type GaN-base compound semiconductor than a region of the light-permeable electrode in contact with

**PRELIMINARY AMENDMENT**  
**Continuation of Application No. 10/136,377**

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~~the p-type GaN-base compound semiconductor comprises at least one member selected from a group consisting of Ti, In, Mn, Ti, Al, Ag, Sn, AuBe, AuZn, AuMg, AlSi, TiSi and TiBe.~~

Claims 3-36 (canceled).